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(72) Inventors; and

(75) Inventors/Applicants (for US only): **TAKAYA, Hidefumi** [JP/JP]; c/o Toyota Jidosha Kabushiki Kaisha, 1, Toyota-cho, Toyota-shi, Aichi 471-8571 (JP). **HAMADA, Kimimori** [JP/JP]; c/o Toyota Jidosha Kabushiki Kaisha, 1, Toyota-cho, Toyota-shi, Aichi 471-8571 (JP). **KUROY-ANAGI, Akira** [JP/JP]; c/o Denso Corporation, 1-1, Showa-cho, Kariya-shi, Aichi 448-8661 (JP). **OKURA, Yasushi** [JP/JP]; c/o Denso Corporation, 1-1, Showa-cho, Kariya-shi, Aichi 448-8661 (JP). **TOKURA, Norihito** [JP/JP]; c/o Denso Corporation, 1-1, Showa-cho, Kariya-shi, Aichi 448-8661 (JP).

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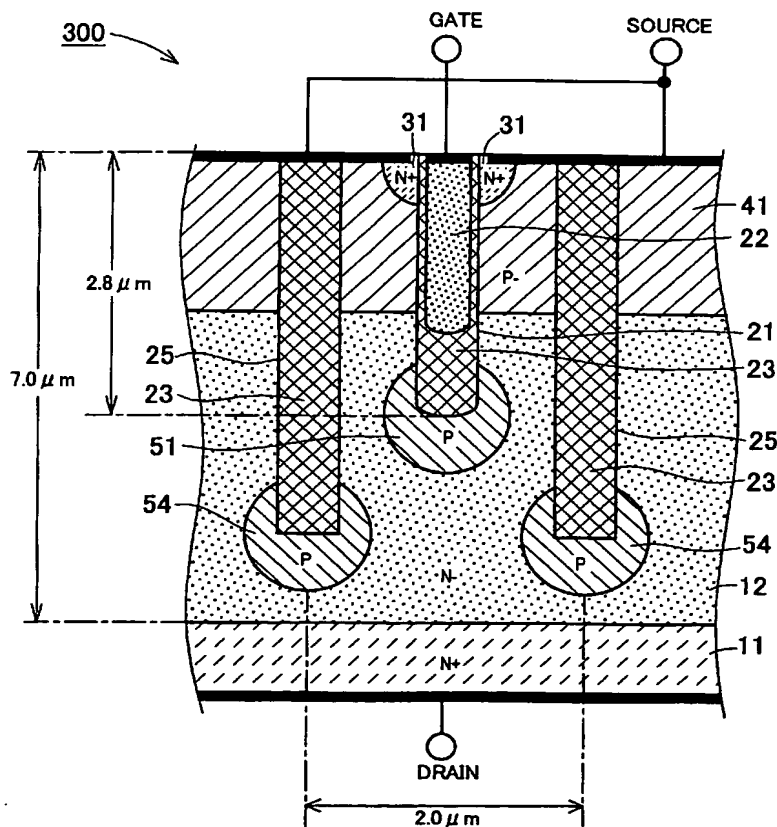
(71) Applicants (for all designated States except US): **TOYOTA JIDOSHA KABUSHIKI KAISHA** [JP/JP]; 1, Toyota-cho, Toyota-shi, Aichi 471-8571 (JP). **DENSO CORPORATION** [JP/JP]; 1-1, Showa-cho, Kariya-shi, Aichi 448-8661 (JP).

(74) Agents: **OKADO, Akiyoshi** et al.; Nagoya Center Building, Annex 2nd Floor, 2-22, Nishiki 2-chome, Naka-ku, Nagoya-shi, Aichi 460-0003 (JP).

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(54) Title: INSULATED GATE TYPE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF



(57) Abstract: The invention is intended to present an insulated gate type semiconductor device that can be manufactured easily and its manufacturing method while realizing both higher withstand voltage design and lower on-resistance design. The semiconductor device comprises N+ source region 31, N+ drain region 11, P- body region 41, and N- drift region 12. By excavating part of the upper side of the semiconductor device, a gate trench 21 is formed. The gate trench 21 incorporates the gate electrode 22. A P floating region 51 is provided beneath the gate trench 21. A further trench 35 differing in depth from the gate trench 21 may be formed, a P floating region 54 being provided beneath the trench 25.



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